

TPIC6259 POWER LOGIC 8-BIT ADDRESSABLE LATCH

SLIS009A – APIRL 1992 – REVISED SEPTEMBER 1995

- Low $r_{DS(on)}$. . . 1.3 Ω Typical
- Avalanche Energy . . . 75 mJ
- Eight Power DMOS Transistor Outputs of 250-mA Continuous Current
- 1.5-A Pulsed Current Per Output
- Output Clamp Voltage at 45 V
- Four Distinct Function Modes
- Low Power Consumption

description

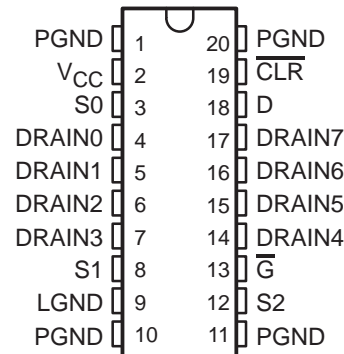
This power logic 8-bit addressable latch controls open-drain DMOS transistor outputs and is designed for general-purpose storage applications in digital systems. Specific uses include working registers, serial-holding registers, and decoders or demultiplexers. This is a multi-functional device capable of storing single-line data in eight addressable latches with 3-to-8 decoding or demultiplexing mode active-low DMOS outputs.

Four distinct modes of operation are selectable by controlling the clear (\overline{CLR}) and enable (\overline{G}) inputs as enumerated in the function table. In the addressable-latch mode, data at the data-in (D) terminal is written into the addressed latch. The addressed DMOS transistor output inverts the data input with all unaddressed DMOS-transistor outputs remaining in their previous states. In the memory mode, all DMOS-transistor outputs remain in their previous states and are unaffected by the data or address inputs. To eliminate the possibility of entering erroneous data in the latch, enable \overline{G} should be held high (inactive) while the address lines are changing. In the 3-to-8 decoding or demultiplexing mode, the addressed output is inverted with respect to the D input and all other outputs are high. In the clear mode, all outputs are high and unaffected by the address and data inputs.

Separate power and logic level ground pins are provided to facilitate maximum system flexibility. Pins 1, 10, 11, and 20 are internally connected, and each pin must be externally connected to the power system ground in order to minimize parasitic inductance. A single-point connection between pin 9, logic ground (LGND), and pins 1, 10, 11, and 20, power ground (PGND) must be externally made in a manner that reduces crosstalk between the logic and load circuits.

The TPIC6259 is characterized for operation over the operating case temperature range of -40°C to 125°C .

DW OR N PACKAGE
(TOP VIEW)



FUNCTION TABLE

INPUTS			OUTPUT OF ADDRESSED DRAIN	EACH OTHER DRAIN	FUNCTION
\overline{CLR}	\overline{G}	D			
H	L	H	L	Q_{iO}	Addressable Latch
H	L	L	H	Q_{iO}	
H	H	X	Q_{iO}	Q_{iO}	Memory
L	L	H	L	H	8-Line Demultiplexer
L	L	L	H	H	
L	H	X	H	H	Clear

LATCH SELECTION TABLE

SELECT INPUTS			DRAIN ADDRESSED
S2	S1	S0	
L	L	L	0
L	L	H	1
L	H	L	2
L	H	H	3
H	L	L	4
H	L	H	5
H	H	L	6
H	H	H	7



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS
INSTRUMENTS**

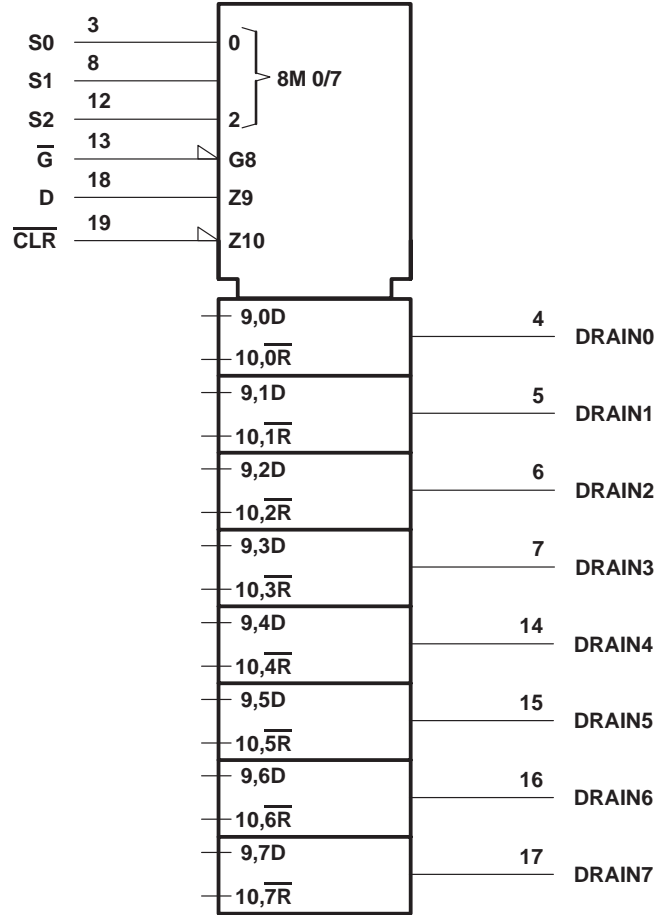
Copyright © 1995, Texas Instruments Incorporated

POST OFFICE BOX 655303 • DALLAS, TEXAS 75265
POST OFFICE BOX 1443 • HOUSTON, TEXAS 77251-1443

TPIC6259 POWER LOGIC 8-BIT ADDRESSABLE LATCH

SLIS009A – APIRL 1992 – REVISED SEPTEMBER 1995

logic symbol†

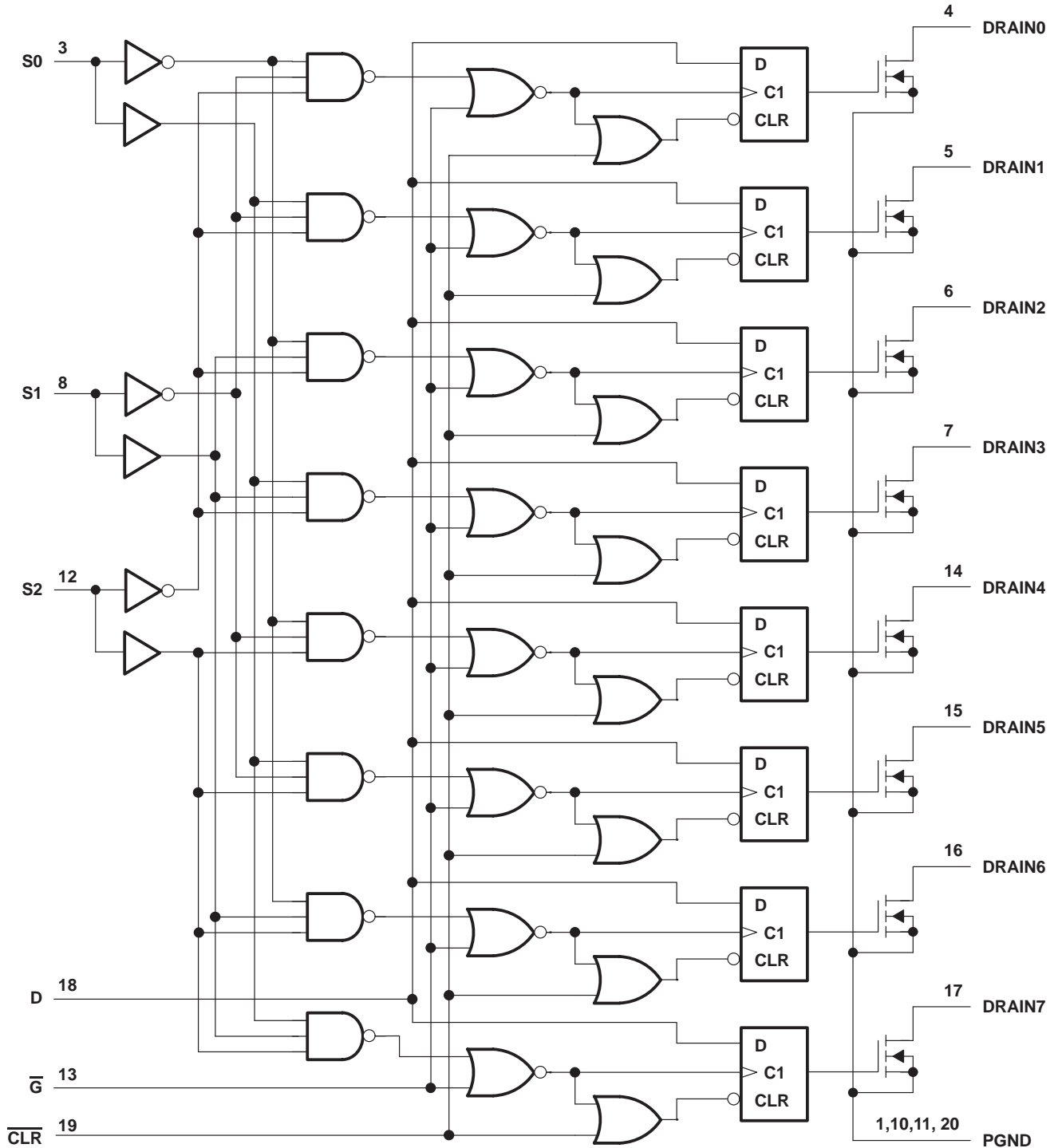


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

TPIC6259 POWER LOGIC 8-BIT ADDRESSABLE LATCH

SLIS009A – APIRL 1992 – REVISED SEPTEMBER 1995

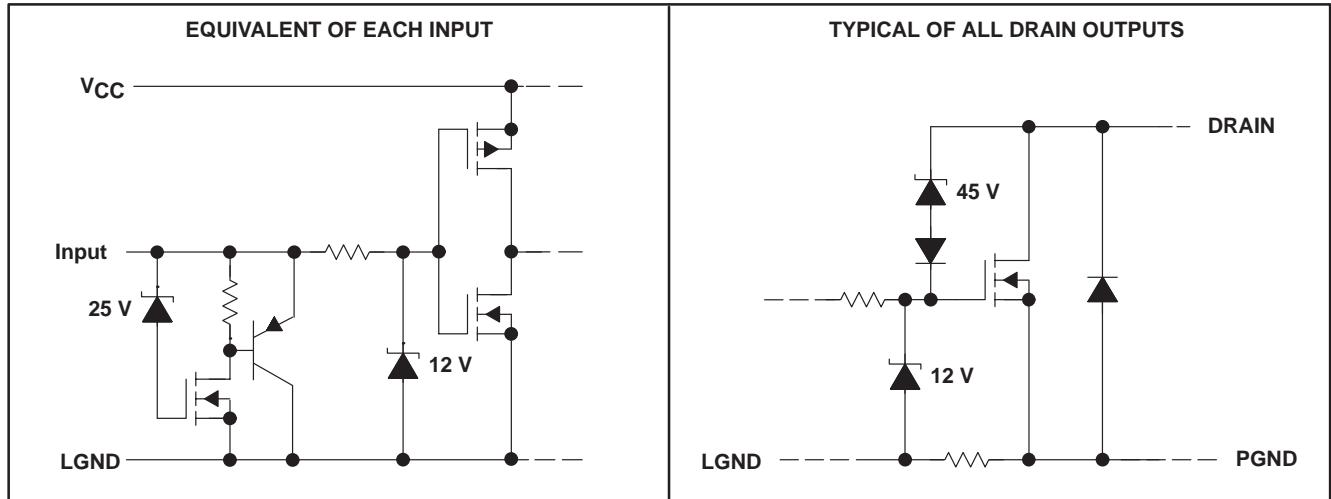
logic diagram (positive logic)



TPIC6259 POWER LOGIC 8-BIT ADDRESSABLE LATCH

SLIS009A – APIRL 1992 – REVISED SEPTEMBER 1995

schematic of inputs and outputs



absolute maximum ratings over the recommended operating case temperature range (unless otherwise noted)†

Logic supply voltage, V_{CC} (see Note 1)	7 V
Logic input voltage range, V_I	-0.3 V to 7 V
Power DMOS drain-to-source voltage, V_{DS} (see Note 2)	45 V
Continuous source-drain diode anode current	1 A
Pulsed source-drain diode anode current	2 A
Pulsed drain current, each output, all outputs on, I_{Dn} , $T_A = 25^\circ\text{C}$ (see Note 3)	750 mA
Continuous drain current, each output, all outputs on, I_{Dn} , $T_A = 25^\circ\text{C}$	250 mA
Peak drain current single output, I_{DM} , $T_A = 25^\circ\text{C}$ (see Note 3)	2 A
Single-pulse avalanche energy, E_{AS} (see Note 4)	75 mJ
Avalanche current, I_{AS} (see Note 4)	1 A
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T_J	-40°C to 150°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
- All voltage values are with respect to LGND and PGND.
 - Each power DMOS source is internally connected to PGND.
 - Pulse duration $\leq 100 \mu\text{s}$, duty cycle $\leq 2\%$
 - DRAIN supply voltage = 15 V, starting junction temperature, $(T_{JS}) = 25^\circ\text{C}$, $L = 100 \text{ mH}$, $I_{AS} = 1 \text{ A}$ (see Figure 4).

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 125^\circ\text{C}$ POWER RATING
DW	1125 mW	9.0 mW/°C	225 mW
N	1150 mW	9.2 mW/°C	230 mW

TPIC6259
POWER LOGIC 8-BIT ADDRESSABLE LATCH

SLIS009A – APIRL 1992 – REVISED SEPTEMBER 1995

recommended operating conditions over recommended operating temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Logic supply voltage, V_{CC}	4.5	5.5	V
High-level input voltage, V_{IH}	0.85 V_{CC}		V
Low-level input voltage, V_{IL}	0.15 V_{CC}		V
Pulsed drain output current, $T_C = 25^\circ\text{C}$, $V_{CC} = 5\text{ V}$ (see Notes 3 and 5)	-1.8	1.5	A
Setup time, D high before $\overline{G}\uparrow$, t_{SU} (see Figure 2)	10		ns
Hold time, D high after $\overline{G}\uparrow$, t_H (see Figure 2)	5		ns
Pulse duration, t_W (see Figure 2)	15		ns
Operating case temperature, T_C	-40	125	$^\circ\text{C}$

electrical characteristics, $V_{CC} = 5\text{ V}$, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$ Drain-source breakdown voltage	$I_D = 1\text{ mA}$	45			V
V_{SD} Source-drain diode forward voltage	$I_F = 250\text{ mA}$, See Note 3		0.85	1	V
I_{IH} High-level input current	$V_{CC} = 5.5\text{ V}$, $V_I = V_{CC}$			1	μA
I_{IL} Low-level input current	$V_{CC} = 5.5\text{ V}$, $V_I = 0$			-1	μA
I_{CC} Logic supply current	$I_O = 0$, All inputs low		15	100	μA
I_N Nominal current	$V_{DS(on)} = 0.5\text{ V}$, $I_N = I_D$, $T_C = 85^\circ\text{C}$, See Notes 5, 6, and 7		250		mA
I_{DSX} Off-state drain current	$V_{DS} = 40\text{ V}$		0.05	1	μA
	$V_{DS} = 40\text{ V}$, $T_C = 125^\circ\text{C}$		0.15	5	
$r_{DS(on)}$ Static drain-source on-state resistance	$I_D = 250\text{ mA}$, $V_{CC} = 4.5\text{ V}$	See Notes 5 and 6 and Figures 8 and 9	1.3	2	Ω
	$I_D = 250\text{ mA}$, $T_C = 125^\circ\text{C}$, $V_{CC} = 4.5\text{ V}$		2	3.2	
	$I_D = 500\text{ mA}$, $V_{CC} = 4.5\text{ V}$		1.3	2	

switching characteristics, $V_{CC} = 5\text{ V}$, $T_C = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} Propagation delay time, low-to-high-level output from D	$C_L = 30\text{ pF}$, $I_D = 250\text{ mA}$, See Figures 1, 2, and 10		625		ns
t_{PHL} Propagation delay time, high-to-low-level output from D			140		ns
t_r Rise time, drain output			650		ns
t_f Fall time, drain output			400		ns
t_a Reverse-recovery-current rise time	$I_F = 250\text{ mA}$, $di/dt = 20\text{ A}/\mu\text{s}$, See Notes 5 and 6 and Figure 3		100		ns
t_{rr} Reverse-recovery time			300		

- NOTES: 3. Pulse duration $\leq 100\ \mu\text{s}$, duty cycle $\leq 2\%$
5. Technique should limit $T_J - T_C$ to 10°C maximum.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at $T_C = 85^\circ\text{C}$.

thermal resistance

PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
$R_{\theta JA}$ Thermal resistance junction-to-ambient	DW package		111	$^\circ\text{C}/\text{W}$
	N package	All 8 outputs with equal power	108	



TPIC6259 POWER LOGIC 8-BIT ADDRESSABLE LATCH

SLIS009A – APIRL 1992 – REVISED SEPTEMBER 1995

PARAMETER MEASUREMENT INFORMATION

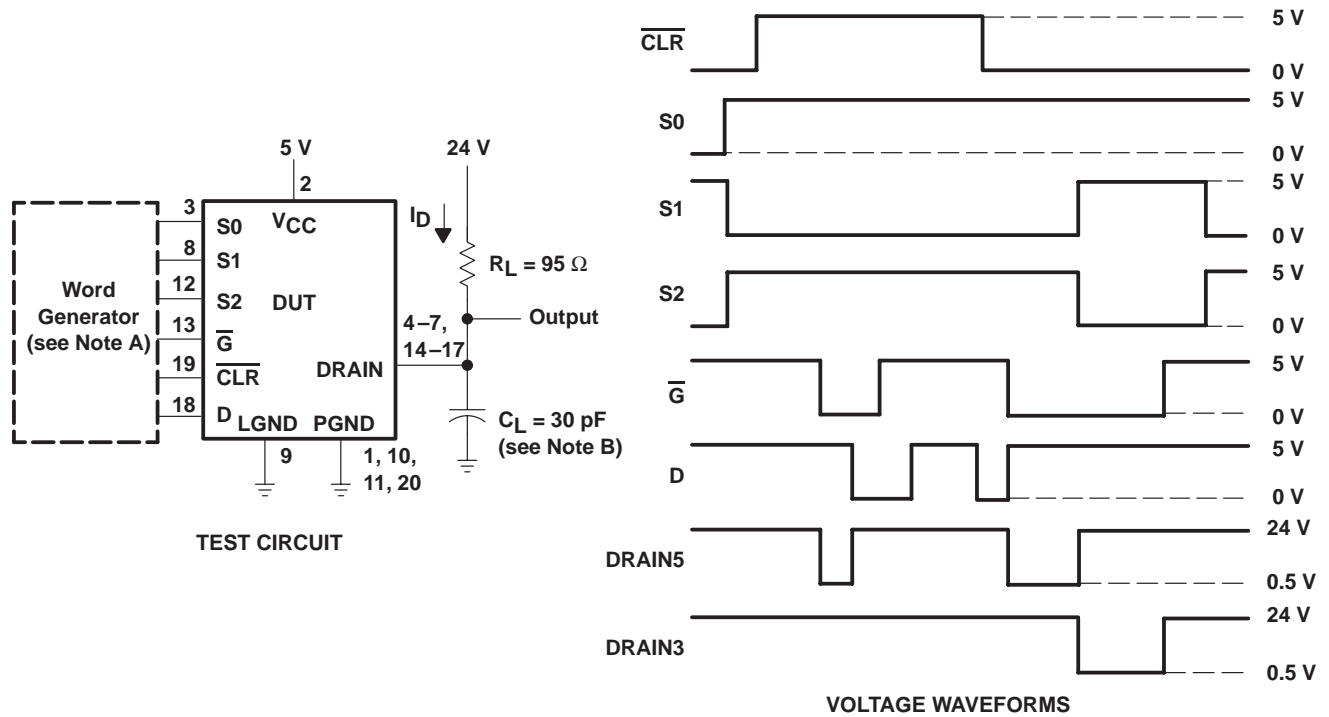


Figure 1. Typical Operation Mode

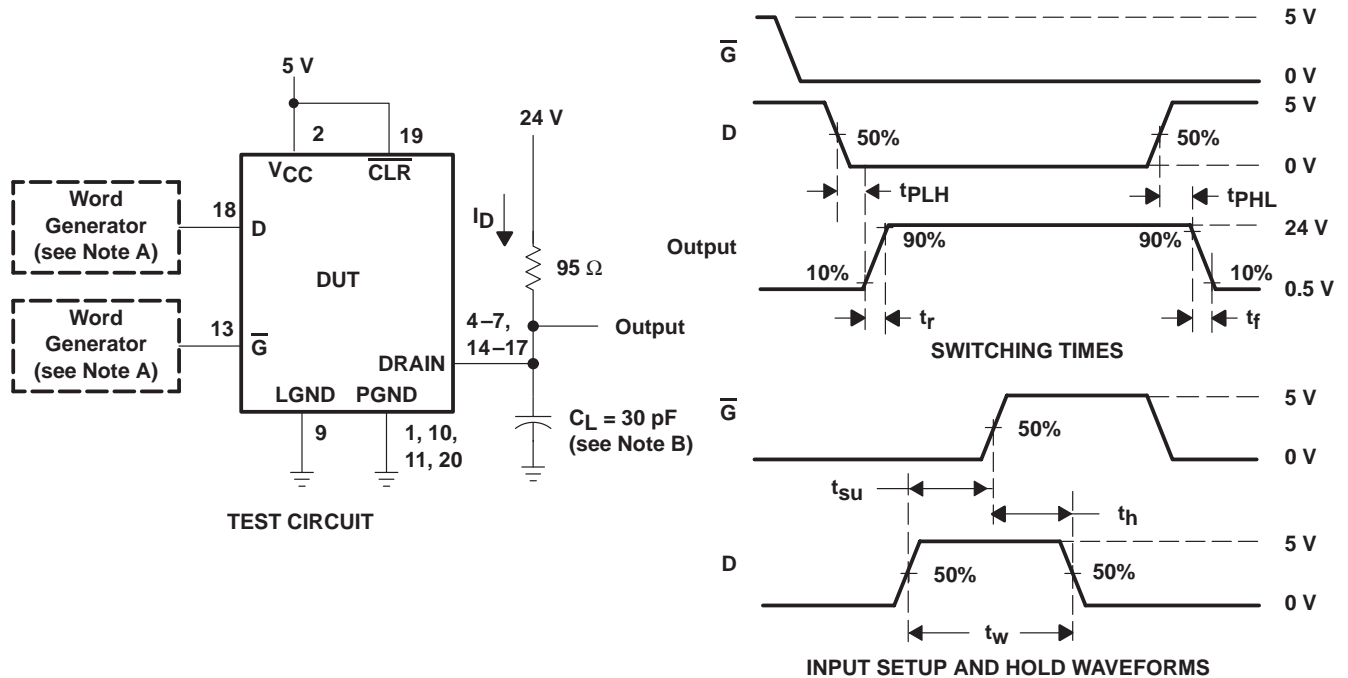
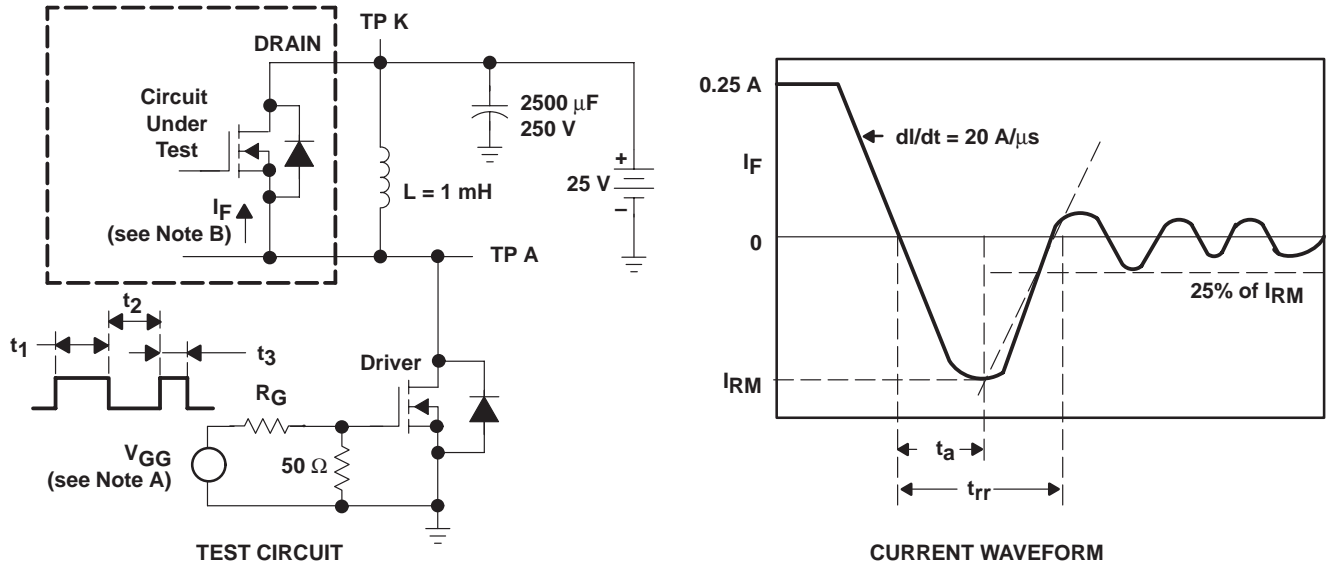


Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

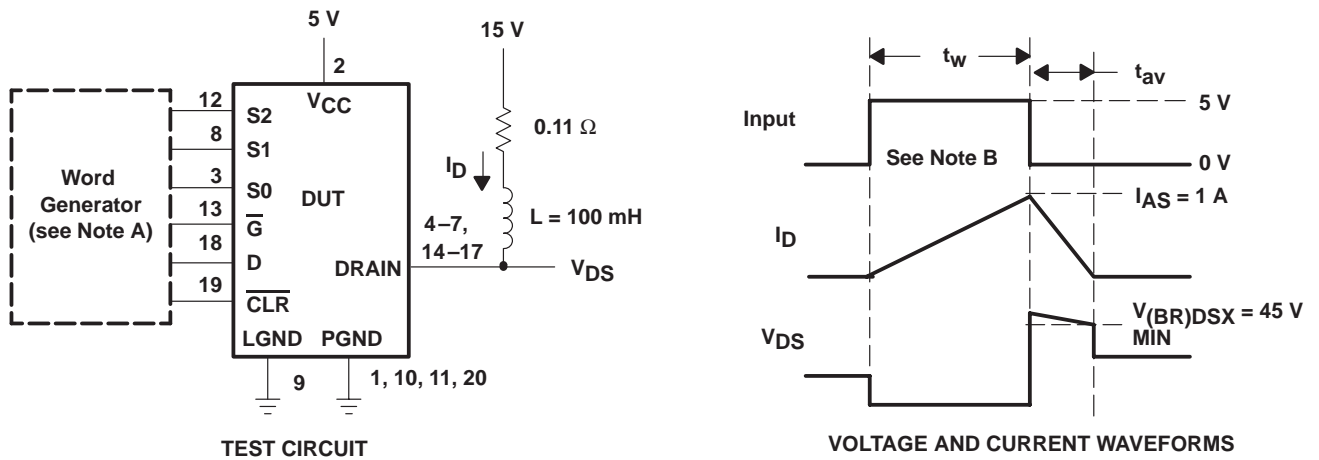
- NOTES: A. The word generator has the following characteristics: $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$, $t_w = 300 \text{ ns}$, pulsed repetition rate (PRR) = 5 kHz, $Z_O = 50 \Omega$.
B. C_L includes probe and jig capacitance.

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The V_{GG} amplitude and R_G are adjusted for $di/dt = 20 \text{ A}/\mu\text{s}$. A V_{GG} double-pulse train is used to set $I_F = 0.25 \text{ A}$, where $t_1 = 10 \mu\text{s}$, $t_2 = 7 \mu\text{s}$, and $t_3 = 3 \mu\text{s}$.
B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode



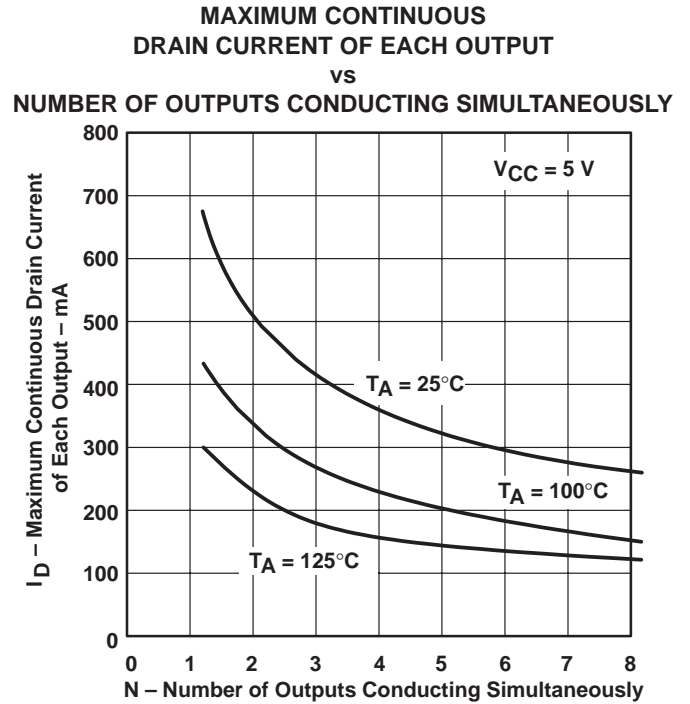
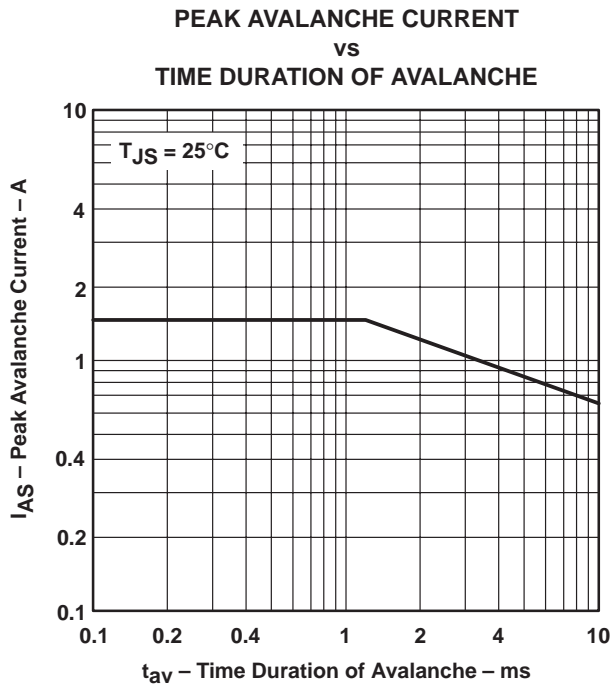
- NOTES: A. The pulse generator has the following characteristics: $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$, $Z_0 = 50 \Omega$.
B. Input pulse duration, t_w , is increased until peak current $I_{AS} = 1 \text{ A}$.
Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 75 \text{ mJ}$.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

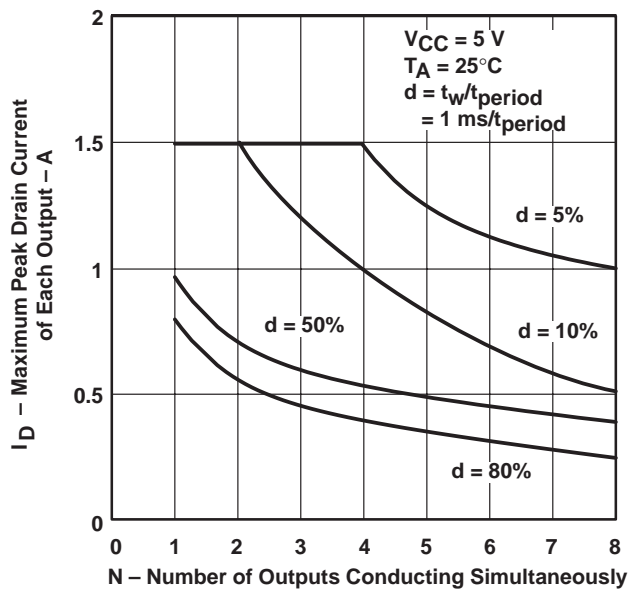
TPIC6259 POWER LOGIC 8-BIT ADDRESSABLE LATCH

SLIS009A – APIRL 1992 – REVISED SEPTEMBER 1995

TYPICAL CHARACTERISTICS



**MAXIMUM PEAK DRAIN CURRENT
OF EACH OUTPUT
vs
NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY**



TYPICAL CHARACTERISTICS

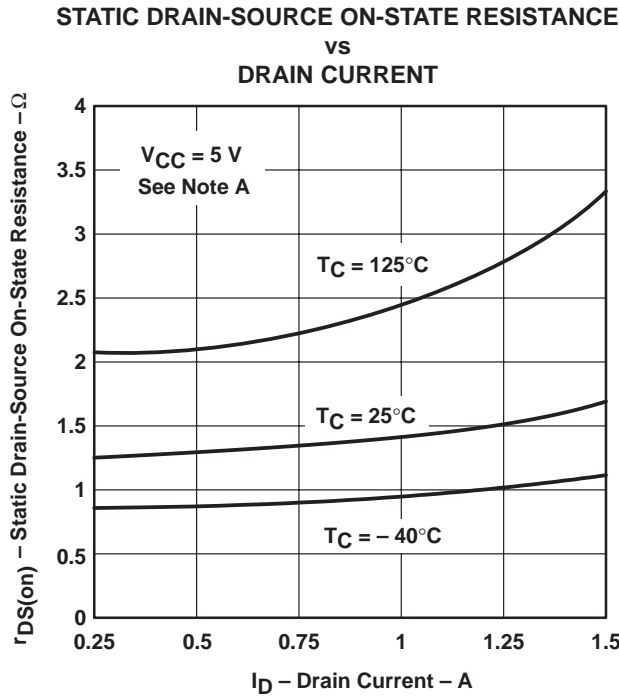


Figure 8

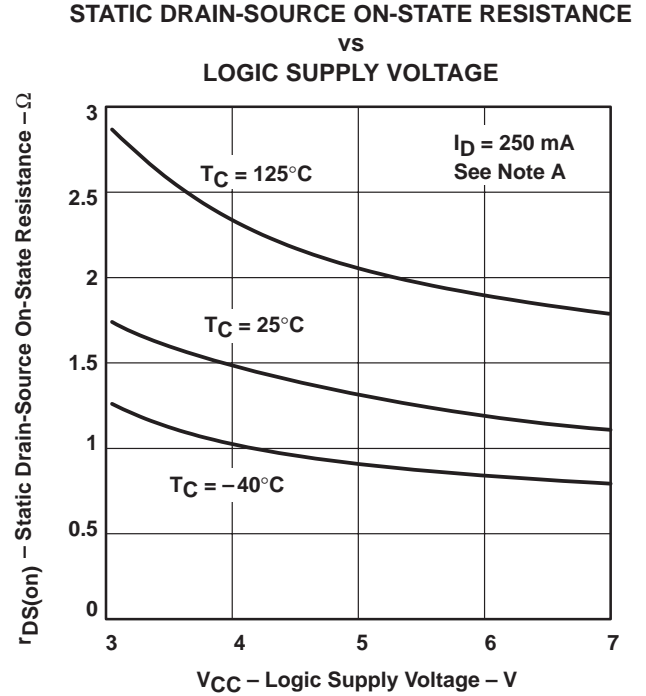


Figure 9

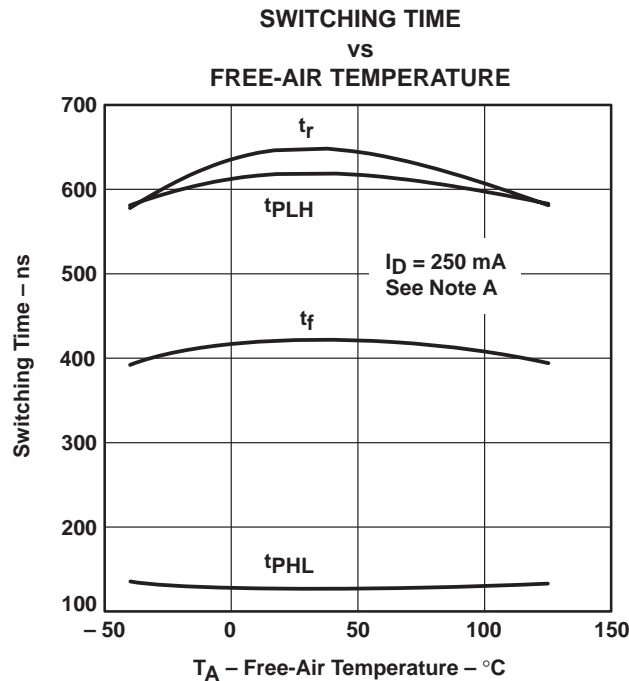


Figure 10

NOTE A: Technique should limit $T_J - T_C$ to 10°C maximum.

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.